

SMALL SIGNAL DUAL DIODE

FEATURES

- * Silicon epitaxial planar diode
- * Fast switching
- * Surface mounting device

MECHANICAL DATA

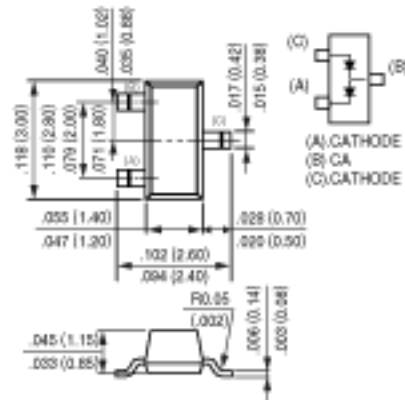
- * Epoxy : Device has UL flammability classification 94V-0
- * Weight : approx. 0.008g

MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Ratings at 25 °C ambient temperature unless otherwise specified.
 Single phase, half wave, 60 Hz, resistive or inductive load.
 For capacitive load, derate current by 20%.



SOT-23



Dimensions in inches and (millimeters)

MAXIMUM RATINGS (At $T_A = 25^\circ\text{C}$ unless otherwise noted)

RATINGS	SYMBOL	BAV99	UNITS
Repetitive Peak Reverse Voltage	V_{RRM}	70	Volts
Forward Continuous Current at $T_A=25^\circ\text{C}$	I_F	150	mA
Repetitive Peak Forward Current at $T_A=25^\circ\text{C}$	I_{FM}	500	mA
Surge Forward Current at $t_p < 1 \text{ s}$, at $T_A=25^\circ\text{C}$	I_{FSM}	1000	mA
Total Power Dissipation	P_D	250	mW
Junction Temperature	T_J	125	$^\circ\text{C}$
Storage Temperature Range	T_{STG}	-65 to +150	$^\circ\text{C}$

ELECTRICAL CHARACTERISTICS (At Ta = 25°C unless otherwise noted)

CHARACTERISTICS	SYMBOL	Value	Unit	Testing Condition
Reverse Breakdown Voltage	V(BR)R	70	V	I _r =100µA
Forward Voltage	V _F (1)	715	mV	I _F =1mA
	V _F (2)	855	mV	I _F =10mA
	V _F (3)	1000	mV	I _F =50mA
	V _F (4)	1250	mV	I _F =150mA
Reverse Current	I _r	2.5	µA	V _r =70V
Total Capacitance	C _t	1.5	pF	V _r =0V, f=1MHz
Reverse Recovery Time	T _{rr}	6	nS	I _F /I _r =10mA, R _L =100 ohm, measured at I _F =1mA

CHARACTERISTIC CURVES

FIG. 1 - FORWARD CURRENT & FORWARD VOLTAGE

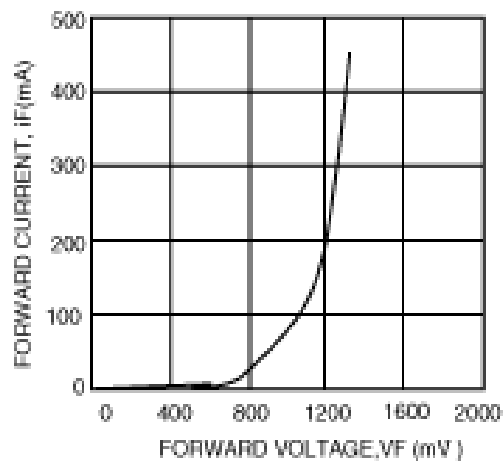


FIG. 2 - DIODE CAPACITANCE

